

CXTA27
SURFACE MOUNT
NPN SILICON
DARLINGTON TRANSISTOR

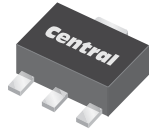


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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CXTA27 type is a NPN Silicon Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

MARKING: FULL PART NUMBER



SOT-89 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Emitter Voltage	V_{CES}	60	V
Emitter-Base Voltage	V_{EBO}	10	V
Continuous Collector Current	I_C	500	mA
Power Dissipation	P_D	1.2	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	104	$^\circ\text{C/W}$

SYMBOL

V_{CES}	60	V
V_{EBO}	10	V
I_C	500	mA
P_D	1.2	W
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	104	$^\circ\text{C/W}$

UNITS

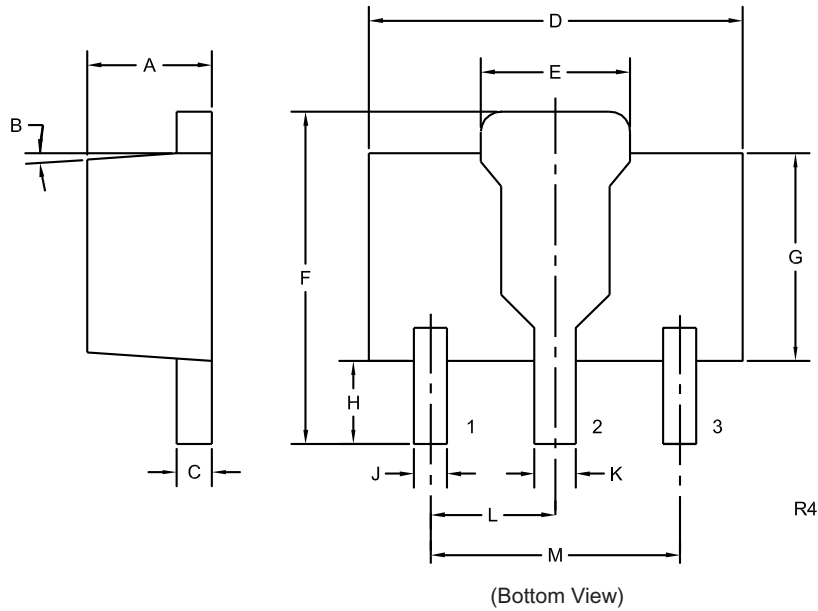
ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=50\text{V}$		100	nA
I_{CES}	$V_{CE}=50\text{V}$		500	nA
I_{EBO}	$V_{EB}=10\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	60		V
BV_{CES}	$I_C=100\mu\text{A}$	60		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=0.1\text{mA}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$		2.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	10,000		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	10,000		
f_T	$V_{CE}=50\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	125		MHz

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SOT-89 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Emitter
- 2) Collector
- 3) Base

MARKING:
FULL PART NUMBER

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.014	0.018	0.35	0.46
D	0.173	0.185	4.40	4.70
E	0.064	0.074	1.62	1.87
F	0.146	0.177	3.70	4.50
G	0.090	0.106	2.29	2.70
H	0.028	0.051	0.70	1.30
J	0.014	0.019	0.36	0.48
K	0.017	0.023	0.44	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R4)

R4 (23-February 2010)